

LL103A / 103B / 103C

94 9371

Vishay Semiconductors

Small Signal Schottky Barrier Diodes

Features

- Integrated protection ring against static discharge
- Low capacitance
- Low leakage current
- Low forward voltage drop

Applications

HF-Detector Protection circuit Small battery charger AC-DC/ DC-Dc converters

Mechanical Data

Case: MiniMELF Glass Case (SOD-80) Weight: approx. 31 mg Cathode Band Color: Black Packaging Codes/Options: GS18 / 10 k per 13" reel (8 mm tape), 10 k/box GS08 / 2.5 k per 7" reel (8 mm tape), 12.5 k/box

Parts Table

Part	Type differentiation	Ordering code	Remarks	
LL103A	V_R = 40 V, V_F @ I _F = 20 mA max. 0.37 V	LL103A-GS08 or LL103A-GS18	Tape and Reel	
LL103B	$V_R = 30 \text{ V}, V_F @ I_F = 20 \text{ mA max. } 0.37 \text{ V}$	LL103B-GS08 or LL103B-GS18	Tape and Reel	
LL103C	$V_{R} = 20 \text{ V}, V_{F} @ I_{F} = 20 \text{ mA max. } 0.37 \text{ V}$	LL103C-GS08 or LL103C-GS18	Tape and Reel	

Absolute Maximum Ratings

 T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition Part		Symbol	Value	Unit	
Reverse voltage		LL103A	V _R	40	V	
		LL103B	V _R	30	V	
		LL103C	V _R	20	V	
Forward current			I _{FAV}	200	mA	
Peak forward surge curent	$t_p = 300 \ \mu s$, square pulse		I _{FSM}	15	mW	
Power dissipation	$I = 4 \text{ mm}, T_L = \text{constant}$		P _{tot}	400	mW	

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Thermal Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit	
Junction temperature		Tj	125	°C	
Storage temperature range		T _{stg}	- 65 to + 150	°C	
Junction ambient	$I = 4 \text{ mm}, T_L = \text{constant}$	R _{thJA}	250	K/W	

Electrical Characteristics

 T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Part	Symbol	Min	Тур.	Max	Unit
Reverse breakdown voltage	I _R = 50 μA	LL103A	I _R	40			V
		LL103B	I _R	30			V
		LL103C	I _R	20			V
Leakage current	V _R = 30 V	LL103A	I _R			5	μA
	V _R = 20 V	LL103B	I _R			5	μΑ
	V _R = 10 V	LL103C	I _R			5	μΑ
Forward voltage drop	I _F = 20 mA		V _F			0.37	V
	I _F = 200 mA		V _F			0.6	V
Junction capacitance	V _R = 0 V, f = 1 MHz		C _{tot}		50		pF
Reverse recovery time	$I_F = I_R = 50$ to 200 mA, recover to 0.1 I_R		t _{rr}		10		ns

Typical Characteristics ($T_{amb} = 25 \text{ °C}$ unless otherwise specified)

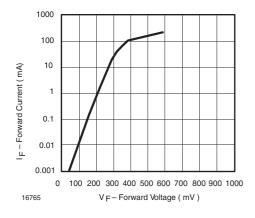


Fig. 1 Forward Current vs. Forward Voltage

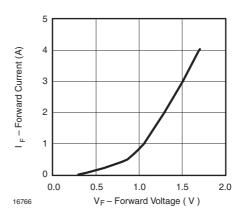


Fig. 2 Forward Current vs. Forward Voltage



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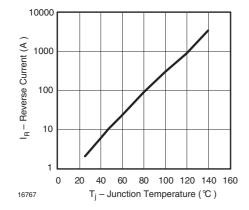


Fig. 3 Reverse Current vs. Junction Temperature

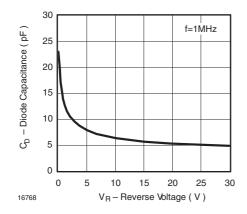


Fig. 4 Diode Capacitance vs. Reverse Voltage

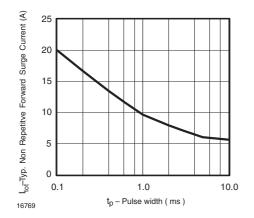
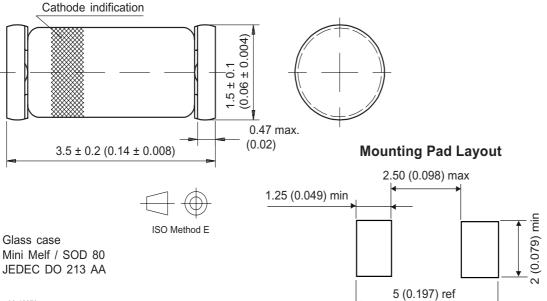


Fig. 5 Typ. Non Repetitive Forward Surge Current vs. Pulse width

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Package Dimensions in mm (Inches)



96 12070





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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operatingsystems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

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